NMR Investigation of Pressure Effect on Intermediate Valence Compound SmB₆

Kohei Nishiyama¹, Takeshi Mito¹, Gabriel Pristáš^{1,2}, Yukiko Hara¹, Takehide Koyama¹, Koichi Ueda¹, Takao Kohara¹, Yuichi Akahama¹, Slavomír Gabáni², Marián Reiffers², Karol Flachbart², Hideto Fukazawa³, Yoh Kohori³, Nao Takeshita⁴, and Natalia Shitsevalova⁵

¹Graduate School of Material Science, University of Hyogo, Hyogo 678-1297, Japan

²Institute of Experimental Physics, Slovak Academy of Science, 04001 Košice, Slovakia

³Graduate School of Science, Chiba University, Chiba 263-8522, Japan

⁴National Institute of Advanced Industrial Science and Technology, Ibaraki 305-8562, Japan

⁵Institute for Problem of Material Science, National Academy of Science of Ukraine, 03680 Kiev, Ukraine

E-mail: mito@sci.u-hyogo.ac.jp

(Received October 18, 2013)

We have carried out ¹¹B-nuclear magnetic resonance (NMR) and X-ray diffraction measurements on the intermediate valence compound SmB₆ under high pressure. The temperature dependence of nuclear quadrupole resonance frequency ν_Q , obtained from the ¹¹B-NMR measurements, is dominantly contributed from on-site charge distribution. By using a relationship between ν_Q and Sm valence at ambient pressure, we have estimated the pressure dependence of the Sm valence up to 6 GPa. The increase of the Sm valence accelerates with pressure and reaches about 10% increase at 6 GPa. The present result suggests that the pressure-induced localization of Sm 4*f*-hole is responsible for the long-range magnetic order under pressure.

KEYWORDS: NMR, SmB₆, Kondo insulator, intermediate valence, high pressure

1. Introduction

SmB₆ has been intensively studied for more than forty years because of its notable features: for example, intermediate valence state (Sm valence is ~ 2.6 [see Refs. 1 and 2 and references therein]), and semiconducting property, so-called "Kondo insulator", with a narrow-gap (50–100 K [3,4]). The insulating gap of SmB₆ is known to be suppressed by the application of pressure, and subsequently SmB₆ becomes metallic above pressure in the range of 4–7 GPa [5]. Recently, a new magnetically ordered phase has been found above ~ 6 GPa by a high-pressure ¹⁴⁹Sm nuclear forward-scattering measurement, so that interest in this compound has been renewed [6]. The long-range magnetic order in SmB₆ is expected to result from the localization of Sm 4*f* electrons, by considering the general phase diagram of heavy fermion compounds: that is, the magnetic trivalent state of Sm ions (total angular momentum J = 5/2) becomes more stable than the divalent state (J = 0) under pressure, analogous to the case of Yb-based compounds. However, microscopic understanding of P - T phase diagram has been incomplete due to insufficient experimental information on how electronic configuration (or valence) varies as pressure increases toward the critical pressure P_c of the nonmagnetic-magnetic transition.

To address this problem, we have carried out nuclear magnetic resonance (NMR) measurements at B-site under pressure up to 6 GPa, just below P_c . Since nuclear quadrupole moment couples with the electric-field gradient (EFG) at the nuclear position created by surrounding charges, the mea-

surement of the nuclear quadrupole interaction provides microscopic information on charge distribution. In this paper, we extract essential information by comparing *T*- and *P*-dependences of nuclear quadrupole resonance frequency v_Q with those of the lattice parameter. Therefore, we have also carried out high-pressure X-ray diffraction experiments.

2. Experimental Procedure

A high-quality single crystal of SmB₆ was prepared by the floating melting zone technique. We used a single crystalline sample with dimensions about $1 \times 1 \times 1$ mm³ and a powdered sample for NMR experiments at ambient pressure, while high-pressure NMR measurements were performed with the powdered sample. The high pressures above 3 GPa for the NMR measurements were achieved by using a modified Bridgman anvil cell. A sample container made of Teflon was filled with an equal mixture of Fluorinert FC 70 and FC 77 as a pressure-transmitting medium (PTM). The further information on this pressure cell are given elsewhere [7,8]. The NMR measurement at 2 GPa was carried out with a conventional piston-cylinder pressure cell made of nonmagnetic NiCrAl/CuBe alloys with polyethylsiloxane as a PTM. The ¹¹B-NMR measurements were carried out at a fixed field of about 7.5 T by using a standard spin-echo technique with a phase-coherent pulsed spectrometer. The high-pressure X-ray diffraction experiment was carried out using a monochromatic synchrotron radiation source on BL10XU station at SPring-8, Hyogo [9]. The high pressure was generated by using a diamond anvil cell with a mixture of 16:3:1 methanol-ethanol-water as a PTM. Powder diffraction patterns of the sample were collected using an angle-dispersive method.

3. Results and Discussion

The inset of Fig. 1 shows the representative NMR lines central lines $(-1/2 \leftrightarrow 1/2 \text{ transition})$ and quadrupole satellites $(1/2 \leftrightarrow 3/2 \text{ transition})$ at ambient pressure. When magnetic field is applied along the [001] direction of a boron-octahedron B₆, two sets of three resonance lines are observed: one is from two apical borons of a boron-octahedron (denoted by B^{||} in the inset of Fig. 1(a)) and the other is from four plane borons (B[⊥]). v_Q was evaluated by measuring intervals between the two sets of resonance lines indicated by solid and broken arrows. Figure 1(a) shows the *T*-dependence of v_Q , where we plot the mean frequencies of these splits. Generally v_Q is expressed as $v_Q = 3eQV_{zz}/2I(2I+1)$, where V_{zz} is the largest principal axis component of the EFG tensor and *I* is the nuclear spin (I = 3/2 for ¹¹B nucleus). Here, EFG at the B nuclear position consists of two contributions; one comes from ionic charges on all the other lattice sites surrounding the observing B-site and the other comes from intra-atomic charge distribution at the B-site, *i.e.*

$$V_{zz} = V_{zz}^{\text{lattice}} + V_{zz}^{\text{onsite}}.$$
 (1)

If V_{zz}^{lattice} is dominant in the *T*-dependence of V_{zz} , $v_Q (\propto V_{zz})$ will vary roughly as $v_Q \propto 1/V$ from a point charge model, where V is the unit cell volume. However, by comparing the *T*-dependence of 1/V from previous reports [10, 11] (see Fig. 1(a) and (b)), this is obviously contrary to the present case.

On the other hand, we find a resemblance between the *T*-dependences of v_Q and the valence of the boron-octahedron B₆ [see Fig. 1(a) and (c)]. This is natural because, considering Eq. (1), the on-site charge distribution is an alternative physical parameter governing the *T*-variation of V_{zz} . Recently, Mizumaki *et al.* have precisely measured the *T*-dependence of the Sm valence at ambient pressure by the X-ray absorption spectroscopy [12]. We assume $v(B_6) = -v(Sm)$ from charge neutrality consideration, where v(Sm) and $v(B_6)$ are the valences of Sm and B₆, respectively. If we describe $v(Sm) = 2 + n_f$ with n_f as the number of 4f-hole in the J = 5/2 multiplet, $1 - n_f$ is a parameter reflecting $v(B_6)$. In Fig. 1(c), we show the plot of $1 - n_f$ vs *T* at ambient pressure. Both



Fig. 1. (Color online) (a) *T*-dependences of v_Q . Inset: ¹¹B-NMR spectrum of the single crystalline sample for *H* || [001] at 100K and ambient pressure. (b) *T*-dependence of 1/V from Refs. [10, 11] (c) *T*-dependence of $1 - n_f$ estimated from Ref. [12]. Inset: the plot of $1 - n_f$ vs v_Q with temperature as an implicit parameter. The solid and broken lines are least squares linear fits to the data. See text for details.

 v_Q and $1 - n_f$ increase with decreasing temperature, and exhibit a maximum below 50 K. We see a slight difference between the temperatures for the maxima, which might be due to the difference in experimental method. The temperature at which v_Q shows the maximum corresponds to the gap energy estimated from the *T*-dependence of nuclear spin-lattice relaxation rate $1/T_1$ [4]. As shown in the inset of Fig. 1(c), where we plot the data for $T \ge 50$ K, v_Q depends roughly linearly upon $1 - n_f$ within error bars (dotted line) except the data point at 120 K. However, there seems a slight difference in the slope of the linear fit between in the high- and low-temperature regions. This might suggest that, in the semiconducting state, the contributions to v_Q and/or $1 - n_f$ from conduction electrons differs from those in the metallic state. We therefore adopt a linear fit in the relatively lower-temperature region (solid line) for the following analysis.

Next, as we did in the study at ambient pressure, we compare the data of v_Q and V in the high pressure region. First, we show the results of the high-pressure X-ray diffraction experiment. Figure 2(a) shows the X-ray diffraction patterns of SmB₆ at different pressures up to 9.9 GPa. The P-dependence of V is shown in Fig. 2(b), along with the data from Ref. [13]. Obviously, the accuracy of the present measurement is markedly improved compared to the previous data reported in 1980s [13]. A bulk modulus $B_0 = 144$ GPa and its pressure derivative $B'_0 = 6.4$ have been obtained by fitting the present



Fig. 2. (Color online) (a) Powder x-ray diffraction patterns of SmB_6 at room temperature and at different pressures up to 9.9 GPa. (b) *P*-dependence of *V* estimated from the data in Fig. 2(a), together with previous data [13] for comparison. The solid line is a least-square fit to the Murnaghan-Birch equation.

data for $P \le 9.1$ GPa to the Murnaghan-Birch equation [14],

$$P = \frac{3}{2}B_0 \left[\left(\frac{V}{V_0} \right)^{-\frac{7}{3}} - \left(\frac{V}{V_0} \right)^{-\frac{5}{3}} \right] \left\{ 1 - \frac{3}{4}(4 - B'_0) \left[\left(\frac{V}{V_0} \right)^{-\frac{2}{3}} - 1 \right] \right\},\tag{2}$$

Present B_0 is rather consistent with the value described in Ref. [6] than in Ref. [13].

In Fig. 3(a), we shows the *P*-dependence of v_0 up to 6 GPa evaluated from the measurement of NMR spectra at 2 K. We also plot the *P*-dependence of 1/V in Fig. 3(b). v_0 reveals a more rapid decrease with increasing pressure, which is against the expectation from the scenario that V_{77}^{lattice} is dominant in the P-dependences of V_{zz} . Thus, both P- and T-dependences of v_0 indicate that 1/V is not a proper parameter of determining $v_{\rm O}$. We apply the linear relationship between $v_{\rm O}$ and $1 - n_f$ obtained at ambient pressure to the P-variation of v_Q and roughly estimate v(Sm) under pressure. From Fig. 3(a), v_Q is reduced by about 9 % as pressure increases from ambient pressure to 6 GPa. Then, $1 - n_f$ at 6 GPa is estimated to be 0.23 ± 0.08 from the present assumption, corresponding to $v(Sm) = 2.77 \pm 0.08$. According to the previous measurement of Raman scattering spectrum under pressure [15], the Sm ions of SmB_6 is expected to be trivalent above 20 GPa and at room temperature. Our estimation of v(Sm) at 6 GPa is consistent with the extrapolated value (~ 2.78 at 6 GPa) using the Raman scattering data. However, as seen in Fig. 3(c), the present result indicates that the pressureinduced variation of v(Sm) accelerates with increasing pressure, rather than changes linearly against pressure as reported in Ref. [15]. The discrepancy may arise from the difference in experimental conditions: namely, present measurement of v_0 was carried out at 2 K, much lower than the Kondo temperature of SmB₆, while the Raman scattering was performed at room temperature.



Fig. 3. (Color online) (a) *P*-dependence of v_Q estimated by fitting the powder patterns as shown in the inset. Inset: ¹¹B-NMR spectrum at 6 GPa. (b) *P*-dependence of 1/V evaluated from the data in Fig. 2(b). (c) *P*-dependence of Sm valence estimated by using the linear relationship v_Q and $1 - n_f$.

4. Conclusion

We have carried out ¹¹B-nuclear magnetic resonance (NMR) and X-ray diffraction measurements on SmB₆ under high pressure. The X-ray diffraction pattern does not show any anomaly up to 9.1 GPa, and the *P*-dependence of the lattice constant was precisely determined with advantage of recent improved experimental techniques using the synchrotron facility. The *T*-dependence of v_Q is dominantly contributed from the on-site charge distribution, rather than that from the lattice. By applying the relationship between v_Q and Sm valence at ambient pressure to the *P*-variation of v_Q , we have found that the Sm valence increases by about 10% at 6 GPa. The present result supports the scenario that the pressure-induced localization of Sm 4*f*-hole gives rise to the long-range magnetic order in SmB₆, similar to the general phase diagram for Kondo lattice systems.

5. Acknowledgement

We thank H. Harima, H. Tou, and M. Mizumaki for valuable discussions. This work was supported by JSPS KAKENHI (Grant Nos. 24540349, 21540351, and 22684016), Grants-in-Aid for Scientific Research on Innovative Areas "Heavy Electrons" (Nos. 21102522, 20102005, and 21102505) from MEXT, Hyogo Science and Technology Association, Association of Graduate Schools of Science and Technology, Chiba University, Projects of Slovak Scientific Grant Agency VEGA for Physics (No. 2/0106/13), and the SAS Centre of Excellence: CFNT MVEP. One of the authors (G. P.) was supported by JSPS Postdoctoral Fellowship for Foreign Researchers (No. P09036). The X-ray diffraction measurements were performed at the BL10XU of SPring-8 with the approval of the Japan Synchrotron Radiation Research Institute (JASRI, Proposal No. 2012B1122).

References

- [1] A. Yanase and H. Harima: Prog. Theor. Phys. Suppl. 108 (1992) 19.
- [2] V. N. Antonov, B. N. Harmon, and A. N. Yaresko: Phys. Rev. B 66 (2002) 165209.
- [3] T. Kasuya, K. Takegahara, T. Fujita, T. Tanaka, and E. Bannai: J. Phys. Colloq. 40 (1979) C5-308.
- [4] M. Takigawa, H. Yasuoka, Y. Kitaoka, T. Tanaka, H. Nozaki, and Y. Ishizawa: J. Phys. Soc. Jpn. 50 (1981) 2525.
- [5] For example, S. Gabáni, E. Bauer, S. Berger, K. Flachbart, Y. Paderno, C. Paul, V. Pavlík, and N. Shitsevalova: Phys. Rev. B **67** (2003) 172406, and references therein.
- [6] A. Barla, J. Derr, J. P. Sanchez, B. Salce, G. Lapertot, B. P. Doyle, R. Rüffer, R. Lengsdorf, M. M. Abd-Elmeguid and J. Flouquet: Phys. Rev. Lett. 94 (2005) 166401.
- [7] T. Nakanishi, N. Takeshita and N. Môri: Rev. Sci. Instrum. 73 (2002) 1828.
- [8] H. Fukazawa, N. Yamatoji, Y. Kohori, C. Terakura, N. Takeshita, Y. Tokura and H. Takagi: Rev. Sci. Instrum. 78 (2007) 015106.
- [9] Y. Ohishi, N. Hirao, N. Sata, K. Hirose, and M. Takata: High Pressure Research 28 (2008) 163.
- [10] J. M. Tarascon, Y. Isikawa, B. Chevalier, J. Etourneau, P. Hagenmuller, and M. Kasaya: J. Physique 41 (1980) 1141.
- [11] S. Funahashi, K. Tanaka, and F. Iga: Acta Cryst. B 66 (2010) 292.
- [12] M. Mizumaki, S. Tsutsui and F. Iga: J. Phys: Conf. Ser. 176 (2009) 012034.
- [13] N. B. Brandt, V. V. Moshchalkov, S. N. Pashkevich, M. G. Vybornov, M. V. Semenov, T. N. Kolobyanina, E. S. Konovalova, and Yu. B. Paderno: Solid State Commun. 56 (1985) 937.
- [14] F. Birch: Phys. Rev. 71 (1974) 809.
- [15] N. Ogita, S. Nagai, M. Udagawa, F. Iga, M. Sera, T. Oguchi, J. Akimitsu, and, S.Kunii: Physica B 359-361 (2005) 941.